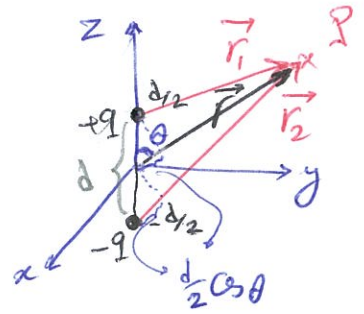


Electric Dipole: Two equal charges of opposite signs that are very close together.



$$V(P(x,y,z)) = \frac{q}{4\pi\epsilon_0} \left[\frac{1}{r_1} - \frac{1}{r_2} \right] = \frac{q}{4\pi\epsilon_0} \left[\frac{r_2 - r_1}{r_1 r_2} \right]$$

If the charges are symmetrically along the z-axis; $r \gg d$:

$$r_1 \approx r - \frac{d}{2} \cos\theta, \quad r_2 \approx r + \frac{d}{2} \cos\theta$$

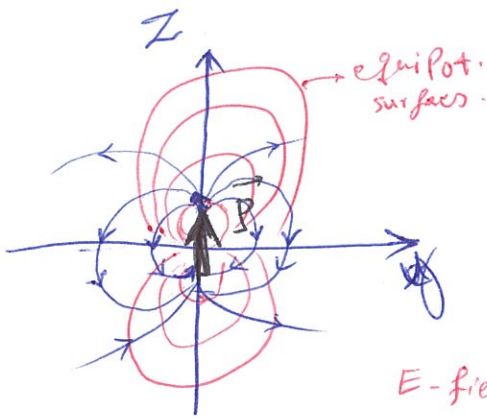
$$\Rightarrow V = \frac{q}{4\pi\epsilon_0} \left[\frac{d \cos\theta}{r^2} \right] \Rightarrow \text{if } \theta = 90^\circ \Rightarrow V = 0 \Rightarrow \text{for a plane } \theta = 90^\circ.$$

→ NO energy expenditure if q moves in this plane.

\vec{P} = dipole moment vector = qd directed from -q to +q.

$$\vec{P} = (qd)\hat{z} \Rightarrow V = \frac{P \cos\theta}{4\pi\epsilon_0 r^2} = \frac{\vec{P} \cdot \hat{r}}{4\pi\epsilon_0 r^2} \rightarrow V \propto \frac{1}{r^2} \text{ for dipole!}$$

* $V_{\text{point charge}} \propto \frac{1}{r}$.



Equipotential surfaces: $\frac{\cos\theta}{r^2} = \text{const.}$

E-fields: $\vec{E} = -\nabla V = \frac{P}{4\pi\epsilon_0 r^3} [2\cos\theta \hat{r} + \sin\theta \hat{\theta}]$

in spherical system $E \propto \frac{1}{r^3}$

$$= 3\cos\theta \hat{r} - (\cos\theta \hat{r} - \sin\theta \hat{\theta})$$

$$= 3\cos\theta \hat{r} - \hat{z}$$

$$\vec{E} = \frac{3(\vec{P} \cdot \hat{r})\hat{r} - r^2 \vec{P}}{4\pi\epsilon_0 r^5}$$

$$\begin{cases} \theta = \pm \frac{\pi}{2} \Rightarrow \vec{E} = E \hat{\theta} = -E \hat{z} \Rightarrow \vec{E} = -\frac{\vec{P}}{4\pi\epsilon_0 r^3} \\ \theta = 0, \pi \Rightarrow \vec{E} \parallel \vec{P} \end{cases}$$

useful for: explaining dielectric in an E-field.

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EX: Hydrogen atom (1p, 1e): An \bar{e} & a Proton separated by 10^{-11} m, symmetrically arranged along z-axis with $z=0$ as its dissecting plane. $\vec{E}(3, 4, 12) = ?$

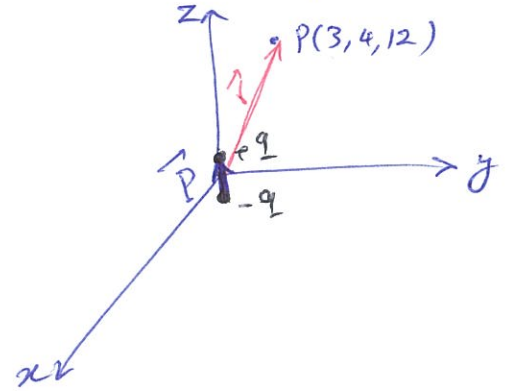
$$\begin{cases} \vec{r} = 3\hat{x} + 4\hat{y} + 12\hat{z} \\ r = 13 \text{ m} \end{cases}$$

$$\vec{P} = qd = (1.6 \times 10^{-19}) (10^{-11}) \hat{z} = 1.6 \times 10^{-30} \hat{z}$$

$$V = \frac{\vec{P} \cdot \vec{r}}{4\pi\epsilon_0 r^3} = \frac{(9 \times 10^9)(1.6 \times 10^{-30} \times 12)}{13^3} = 7.865 \times 10^{-23} \text{ V}$$

$$\vec{E} = \frac{3(\vec{P} \cdot \vec{r})\vec{r} - r^2\vec{P}}{4\pi\epsilon_0 r^5} = \frac{9 \times 10^9}{13^5} \left[3(12 \times 1.6 \times 10^{-30})(3\hat{x} + 4\hat{y} + 12\hat{z}) - 13^2 (1.6 \times 10^{-30}) \hat{z} \right]$$

$$= 10^{-24} \left[4.189 \hat{x} + 5.585 \hat{y} + 10.2 \hat{z} \right] \frac{\text{V}}{\text{m}}$$



materials in an E-field (conductors, semiconductors, insulators):

A. Conductors in E-fields:

- free electron:
- (a) loosely associated with its nucleus
 - (b) free to wander throughout the conductor
 - (c) responds to almost an infinitesimal E-field
 - (d) continues to move as long as it experiences a force.

conductor (metal): has a relatively large # of free \bar{e} .

valance electrons: In the space lattice of metal crystals, there are 1, 2, or 3 valance electrons per atom that are normally free from nucleus.

→ Thermal motion $\approx 10^6$ m/s randomly. ; no net drift ~~in any direction~~ in an isolated conductor (no V across this conductor).

↳ These are electrons in charge of current when we have E-field within a

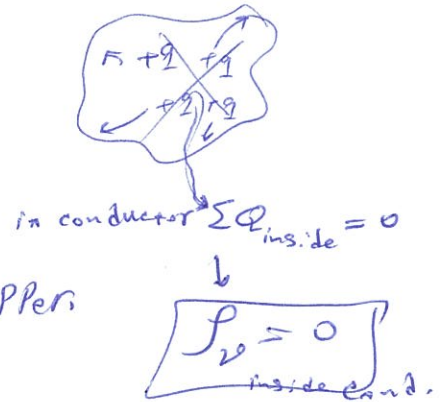
Conductivity: Instead of describing a material in terms of # of free electrons we prefer to describe in terms of conductivity.

conductivity \propto ~~_____~~
 # of valance electrons.

Isolated conductor: # of $+q =$ # of $-q$. (neutral).

excess charge inside a conductor have mutual repulsion till their repulsion is balanced by surface barrier forces. \rightarrow Q goes to surface outside.

$\sim 10^{-14}$ sec. for copper



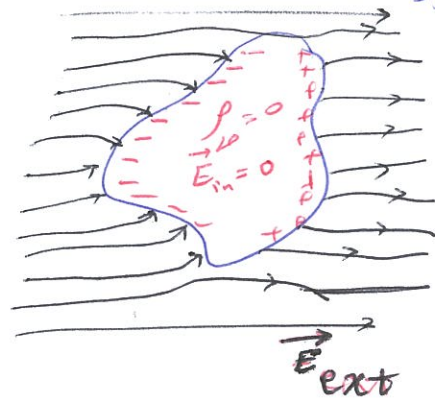
Isolated conductor in E-field:

$\vec{F}_e = -|e|\vec{E}$ \rightarrow move \bar{e} in a direction opposite to \vec{E} . \Rightarrow { One side +, one r - }
 \leftarrow NO contact with conductor. \leftarrow **Induced charge.**

create an E-field equal & opposited to the externally applied E-field.

within conductor: $\vec{E}_{ind} = -\vec{E}_{ext} \Rightarrow \boxed{\vec{E}_{net} = 0}$ inside cond. \rightarrow steady state.

$\vec{E} = -\nabla V \Rightarrow \boxed{V = \text{const.}}$ inside cond. \Rightarrow Conductor is an equipotential region of space.



EX: A spherical region of radius a with uniformly distributed charge ρ_v is in a conducting spherical shell with inner radius b & outer radius c .

Find \vec{E} intensity in all regions.

I) for a sphere of r :
 $(r < a) : Q = \rho_v v = \rho_v \frac{4}{3} \pi r^3$

S_I : Gaussian surface $\oint_{S_I} \vec{E} \cdot d\vec{S} = \frac{Q_{enc}}{\epsilon_0} = \frac{4\rho_v \pi r^3}{3\epsilon_0}$

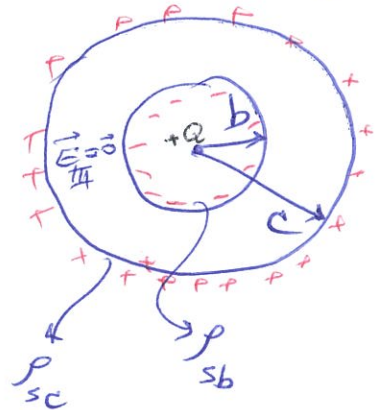
$$\Rightarrow E(4\pi r^2) = \frac{4\pi\rho_v r^3}{3\epsilon_0} \Rightarrow \boxed{\vec{E}_I = \frac{\rho_v r}{3\epsilon_0} \hat{r}} ; 0 < r < a$$

II) $a < r < b$: $\oint_{S_2} \vec{E} \cdot d\vec{S} = \frac{Q_{enc}}{\epsilon_0} \Rightarrow E(4\pi r^2) = \frac{\rho_v v}{\epsilon_0} = \frac{\rho_v \frac{4}{3} \pi a^3}{\epsilon_0} \Rightarrow \boxed{\vec{E}_{II} = \frac{\rho_v a^3}{3\epsilon_0 r^2} \hat{r}}$
 $a < r < b$

III) $b \leq r \leq c$: conductor: $\boxed{\vec{E}_{III} = 0} \Rightarrow$

$$Q_{r=b} = -Q_{0 < r < a} = \frac{4}{3} \pi a^3 \rho_v$$

$$4\pi b^2 \rho_{sb} \Rightarrow \boxed{\rho_{sb} = -\frac{a^3}{3b^2} \rho_v}$$

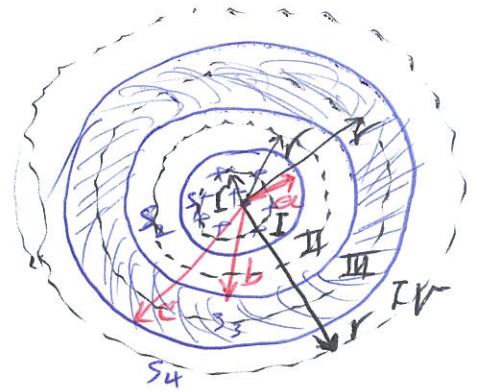


IV) $r \geq c$: outer side of conductor has $+Q$. $\Rightarrow Q_{r=c} = -Q_{r=b}$

$$\Rightarrow 4\pi c^2 \rho_{sc} = +4\pi b^2 \rho_{sb} \Rightarrow \boxed{\rho_{sc} = \frac{b^2}{c^2} \cdot \frac{a^3}{3b^2} \rho_v = \frac{a^3}{3c^2} \rho_v}$$

$$\oint_{S_4} \vec{E} \cdot d\vec{S} = \frac{Q_{enc}}{\epsilon_0} \Rightarrow E(4\pi r^2) = \frac{\frac{4}{3} \pi a^3 \rho_v}{\epsilon_0} \Rightarrow \boxed{\vec{E}_{IV} = \frac{a^3 \rho_v}{3\epsilon_0 r^2} \hat{r}}$$

$$r \geq c.$$



Dielectrics in an E-field: Ideal dielectric (insulator) : is a material with no free-electrons in its lattice structure.

→ No random movements for electrons. → (+) & (-) charges are so sternly bound that they are inseparable.

→ **Distortion:** under the influence of an e-force the molecules of a dielectric sense ~~show~~ a distortion that their centre of (+) charge no longer coincides with the center of a (-) charge ⇒ **Polarization.**



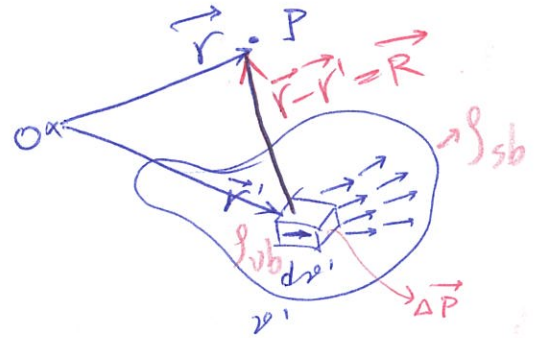
In a Polarized material there are lots of dipoles.



Potential outside a Polarized dielectric:

Polarization vector = $\frac{\text{\# of dipole moments}}{\text{Volume}}$

$$\vec{P} = \lim_{\Delta V \rightarrow 0} \frac{\Delta \vec{P}}{\Delta V} = \frac{d\vec{P}}{dV}$$



$$\rightarrow d\vec{P} = \vec{P} dV' \Rightarrow \int_{V'} dV = \frac{d\vec{P} \cdot \hat{R}}{4\pi\epsilon_0 R^2} = \frac{\vec{P} \cdot \hat{R}}{4\pi\epsilon_0 R^2} dV'$$

Pol. vector

$$\vec{R} = \vec{r} - \vec{r}' = |\vec{r} - \vec{r}'| \hat{R} = R \hat{R}, \quad \vec{\nabla}' \left(\frac{1}{R} \right) = -\frac{1}{R^2} \hat{R}$$

$$\Rightarrow \int_{V'} dV = \frac{\vec{P} \cdot \vec{\nabla}' \left(\frac{1}{R} \right)}{4\pi\epsilon_0} dV' \quad ; \quad \vec{P} \cdot \vec{\nabla}' \left(\frac{1}{R} \right) = \vec{\nabla}' \cdot \left(\frac{\vec{P}}{R} \right) - (\vec{\nabla}' \cdot \vec{P}) / R$$

$$\Rightarrow dV = \frac{1}{4\pi\epsilon_0} \left[\vec{\nabla}' \cdot \left(\frac{\vec{P}}{R} \right) - \frac{\vec{\nabla}' \cdot \vec{P}}{R} \right] dV' \Rightarrow$$

$$V = \frac{1}{4\pi\epsilon_0} \left[\int_{V'} \vec{\nabla}' \cdot \left(\frac{\vec{P}}{R} \right) dV' - \int_{V'} \frac{\vec{\nabla}' \cdot \vec{P}}{R} dV' \right]$$

by divergence theorem:

$$\Rightarrow V = \frac{1}{4\pi\epsilon_0} \oint_{S'} \frac{\vec{P} \cdot \hat{n}}{R} ds' - \frac{1}{4\pi\epsilon_0} \int_{V'} \frac{\nabla' \cdot \vec{P}}{R} dv'$$

Surface term
Volume term

$\rho_{sb} = \vec{P} \cdot \hat{n}$ → bound surface charge density

$\rho_{vb} = -\nabla \cdot \vec{P}$ → bound volume ~ ~

$$\Rightarrow V = \frac{1}{4\pi\epsilon_0} \left[\oint_{S'} \frac{\rho_{sb}}{R} ds' + \int_{V'} \frac{\rho_{vb}}{R} dv' \right]$$

→ Polarization of a dielectric results in bound charges.
 ↓
 Not free, created by separating the charge pairs.

If a dielectric region contains free charge + bound charges:

$\nabla \cdot \vec{E} = \frac{\rho_f + \rho_{vb}}{\epsilon_0} = \frac{\rho_f - \nabla \cdot \vec{P}}{\epsilon_0} \Rightarrow \nabla \cdot (\epsilon_0 \vec{E} + \vec{P}) = \rho_f$ → free charge density

e-field inside the dielectric

we had for free charge that $\nabla \cdot \vec{D} = \rho_f \Rightarrow \vec{D} = \epsilon_0 \vec{E} + \vec{P}$

→ $\nabla \cdot \vec{D}$ will always represent the free charge density of any medium.

effect of Polarization in a dielectric.

→ electric susceptibility.

Linear dielectric: if \vec{P} or $\vec{P} \propto \vec{E} \Rightarrow \vec{P} = \epsilon_0 \chi \vec{E}$

Isotropic dielectric: If the electrical properties of the dielectric are indep. of the direction.

Homogeneous: all portions of the material are identical.

→ class A dielectric . $\Rightarrow \vec{D} = \epsilon_0 (1 + \chi) \vec{E}$ $\epsilon_r = 1 + \chi =$ relative Permittivity or dielectric constant

$\Rightarrow \vec{D} = \epsilon_0 \epsilon_r \vec{E} = \epsilon \vec{E}$ Permittivity of the material

Semiconductors in an e-field:

Semiconductor: a small fraction of the total # of valance electrons are free to move about randomly within space lattice. has some conductivity

→ If we place some excess charge inside a semicond. it will move toward its outer surface due to repulsive forces, but slower rate than conductor

like: Silicon, Germanium

Semicond. in an e-field: The motion of free electrons will cancel the external applied e-field by producing \vec{E}_{in} . $\Rightarrow \vec{E}_{net} = 0 = \vec{E}_{ext} + \vec{E}_{int}$

→ **Electrostatic:** conductors & dielectrics.

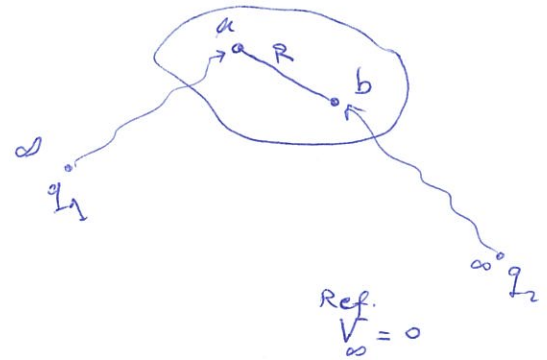
Energy stored in an e-field:

Two methods: - Sources
- Field quantities

$$\begin{cases} W_1 = 0 \\ W_2 = q_2 V_{b,a} = \frac{q_1 q_2}{4\pi \epsilon R} \end{cases} \Rightarrow W_{tot} = W_1 + W_2 = \frac{q_1 q_2}{4\pi \epsilon R}$$

$$\begin{cases} W_1 = q_1 V_{a,b} = \frac{q_1 q_2}{4\pi \epsilon R} \\ W_2 = 0 \end{cases}$$

↓
mutual Pot. energy.
of Two Point charges (d)
in any medium ϵ .



$$\begin{cases} W_1 = 0 \\ W_2 = q_2 V_{b,a} \\ W_3 = q_3 (V_{c,a} + V_{c,b}) \end{cases} \Rightarrow W = \frac{1}{4\pi \epsilon} \left[\frac{q_2 q_1}{R_{21}} + \frac{q_3 q_1}{R_{31}} + \frac{q_3 q_2}{R_{32}} \right]$$

$$\begin{cases} W_3 = 0 \\ W_2 = q_2 (V_{b,c}) \\ W_1 = q_1 (V_{a,c} + V_{a,b}) \end{cases} \Rightarrow W = \frac{1}{4\pi \epsilon} \left[\frac{q_2 q_3}{R_{23}} + \frac{q_1 q_3}{R_{13}} + \frac{q_1 q_2}{R_{12}} \right]$$

$$\Rightarrow W = \frac{1}{2} \left[q_1 (V_{a,c} + V_{a,b}) + q_2 (V_{b,a} + V_{b,c}) + q_3 (V_{c,a} + V_{c,b}) \right]$$

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$$\Rightarrow W = \frac{1}{2} [q_1 V_1 + q_2 V_2 + q_3 V_3] = \frac{1}{2} \sum_{i=1}^3 q_i V_i$$

Pot. at Point a " " b " " c

System of n Point charges $\Rightarrow W = \frac{1}{2} \sum_{i=1}^n q_i V_i$ \rightarrow electrostatic Pot. energy of a group of Point charges in their mutual field.

$$W = \frac{1}{2} \int_V \rho_v V dv$$

ρ_v vol. charge density

$$\rightarrow W = \frac{1}{2} \int_S \rho_s V ds$$

$$W = \frac{1}{2} \int_C \rho_l V dl$$

EX: A metallic sphere of radius 10 cm has a $\rho_s = 10 \frac{nC}{m^2}$ \rightarrow energy stored in this system:

Pot. on the surface of the sphere: $V = \int_S \frac{\rho_s ds}{4\pi\epsilon_0 R} = (9 \times 10^9) (10 \times 10^{-9}) (0.1) \int_0^\pi \sin\theta d\theta \int_0^{2\pi} d\phi$

$\Rightarrow V = 113.1 V = \text{const.}$

$$W = \frac{1}{2} \int_S \rho_s V ds = \frac{1}{2} Q_t V = \frac{1}{2} [4\pi R^2 \rho_s] (113.1) = 71.08 \times 10^{-9} J = 71.08 \text{ nJ}$$

$$W = \frac{1}{2} \int_V \rho_v (\vec{\nabla} \cdot \vec{D}) dv ; \quad \nabla \cdot (\vec{\nabla} \cdot \vec{D}) = \vec{\nabla} \cdot (\nabla V) = -\nabla^2 V$$

$$= \frac{1}{2} \left[\int_V \vec{\nabla} \cdot (\nabla V) dv - \int_V \vec{D} \cdot (\vec{\nabla} V) dv \right]$$

$$= \frac{1}{2} \left[\oint_S \nabla V \cdot d\vec{s} - \int_V \vec{D} \cdot (\vec{\nabla} V) dv \right] \Rightarrow W = \frac{1}{2} \int_V \vec{D} \cdot \vec{E} dv$$

arbitrary surface that bound $v \Rightarrow V, D$ small $\rightarrow \oint \rightarrow 0$

energy density $W = \frac{1}{2} \vec{D} \cdot \vec{E}$ energy per unit volume.
 $= \frac{1}{2} \epsilon E^2 = \frac{1}{2} \epsilon D^2$, $W = \int_V w dv$

\int over all space $R \rightarrow \infty$.

$\frac{1}{2} \rho_v V = w$

energy dens

$W = \frac{1}{2} \rho_v V$ suggest that energy density is Non Zero only where charges exist.

EX: Resolve last example: A metallic sphere with $\rho = 10 \frac{nC}{m^2}$. Energy stored in the system:

$$\oint \vec{D} \cdot d\vec{S} = Q_{enc} \Rightarrow \vec{D} = \frac{Q_{enc}}{4\pi r^2} \hat{r} = \frac{0.1 \times 10^{-9}}{r^2} \hat{r} \left[\frac{C}{m^2} \right]$$

energy density:

$$W = \frac{1}{2} \vec{D} \cdot \vec{E} = \frac{(0.1)^2 \times 10^{-18}}{2 \epsilon_0 r^4} \Rightarrow W = \int_{0.1}^{\infty} \frac{(0.1)^2 \times 10^{-18}}{2 \epsilon_0 r^4} r^2 dr \int_0^{\pi} \sin \theta d\theta \int_0^{2\pi} d\phi$$

$$\Rightarrow W = \left(\frac{(0.1)^2 \times 10^{-18}}{2 \epsilon_0} \left(-\frac{1}{r} \right) \Big|_{0.1}^{\infty} \right) \left(-\cos \theta \Big|_0^{\pi} \right) (2\pi)$$

\downarrow
 $-(-1-1) = +2$

$$= \frac{4\pi (0.01) \times 10^{-18}}{2 \epsilon_0} \left(-\frac{1}{\infty} + \frac{1}{0.1} \right) = \frac{(4\pi)(2\pi)(0.01) \times 10^{-18}}{4\pi \epsilon_0} (0+10)$$

$$= 8\pi^2 (0.01)(10) \times 9 \times 10^9 \times 10^{-18} = 71.06 \text{ nJ.}$$

Boundary Conditions:

Behavior of E-fields at boundary (interface) between two media.

Normal component of \vec{D} :

$$\Delta q = \Delta S \rho_s \quad \leftarrow \oint \vec{D} \cdot d\vec{S} = Q_f$$

$$\vec{D}_1 \cdot \hat{n} \Delta S - \vec{D}_2 \cdot \hat{n} \Delta S = \rho_s \Delta S$$

$$\Rightarrow \hat{n} \cdot (\vec{D}_1 - \vec{D}_2) = \rho_s$$

$\Rightarrow \boxed{D_{n1} - D_{n2} = \rho_s}$ \rightarrow the normal components of the e-flux density are discontinuous if a free surface charge density exists at the interface.

$$\vec{D} = \epsilon \vec{E} \Rightarrow \hat{n} \cdot (\epsilon_1 \vec{E}_1 - \epsilon_2 \vec{E}_2) = \rho_s \Rightarrow \boxed{\epsilon_1 E_{n1} - \epsilon_2 E_{n2} = \rho_s}$$

